

Transistors

General purpose (dual digital transistors) **UMH7N / IMH7A**

● Features

- 1) Includes two DTC143T transistors in a single UMT package.

● Absolute maximum ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V _{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	I _C	100	mA	
Collector power dissipation	UMH7N FMG13, IMH7A	P _C	150 (TOTAL) 300 (TOTAL)	mW *1 *2
Junction temperature	T _J	150	°C	
Storage temperature	T _{STG}	-55 → +150	°C	

*1 120mW per element must not be exceeded.

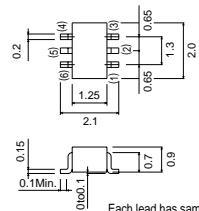
*2 200mW per element must not be exceeded.

- Package, marking, and Packaging specifications

Part No.	UMH7N	IMH7A
Package	UMT6	SMT6
Marking	H7	H7
Code	TR	T108
Basic ordering unit (pieces)	3000	3000

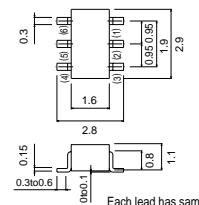
●External dimensions (Units : mm)

UMH7N



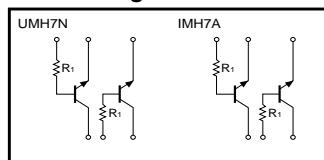
ROHM : UMT6
EIAJ : SC-88

IMH7A



ROHM : SMT6
EIAJ : SC-74

● Circuit diagram



● Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	50	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	50	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=50V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
DC current transfer ratio	h_{FE}	100	250	600	—	$V_{CE} / I_C = 5V / 1mA$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C / I_S = 5mA / 0.25mA$
Input resistance	R_I	3.29	4.7	6.11	$k\Omega$	—